Sommerfeld Integral

Horizontally Oriented Magnetic Dipole above Silver Half-plane

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ELECTRICAL & COMPUTER ENGINEERING

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Introduction

- Semiconductor Heterostructure Interface
- High electron Mobility
- High concentration of electric charge
- Surface waves

Surface Plasmon-Polaritons

Formation of Quantum Well

Two-dimensional confinement of electrons

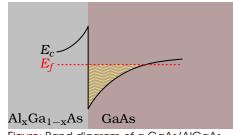


Figure: Band diagram of a GaAs/AlGaAs heterostructure

 $E_c\,$ - Conduction band edge

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 E_f - Fermi level

Material Description

Drude-Lorentz conductivity model

$$\sigma_s(\omega) = \frac{Ne^2\tau}{m^*} \frac{\omega}{\omega + j\tau \left(\omega^2 - \omega_0^2\right)}$$

$$\omega_0 = \chi \sqrt{\frac{Ne^2}{m^* \varepsilon_\infty}}$$

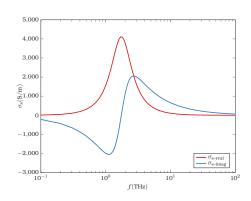
N - charge density (cm^{-3})

 $e\,$ - electron charge

au - scattering time

 m^{st} effective mass of electron

 ω_{0} - effective plasma frequency



 $arepsilon_{\infty}$ high frequency limit of dielectric constan

 χ - geometrical factor (1/3)

Material Description (contd.)

Drude-Lorentz conductivity model

$$\varepsilon(\omega) = \varepsilon^{\infty} + \prod_{i} \frac{\omega_{ii}^{2} - \omega^{2} - j\gamma_{ii}\omega}{\omega_{ii}^{2} - \omega^{2} - j\gamma_{ti}\omega}$$

 $\omega_{t\bar{t}}$ TO phonon frequencies

 ω_{li^-} LO phonon frequencies

 $\gamma\,$ - Damping constants

Dispersion Relation

TE mode

$$k_{z1} + k_{z2} = \omega \sigma_s(\omega)$$

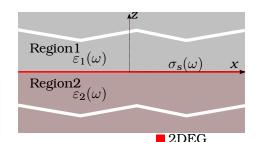
No real solutions for an isotropic environment

TM mode

$$\frac{\varepsilon_1(\omega)}{k_{z1}} + \frac{\varepsilon_2(\omega)}{k_{z2}} = -\frac{\sigma_s(\omega)}{\omega}$$

Real solution(s). Surface waves exist.

$$\begin{aligned} k_{zi} &= \sqrt{k_i^2 - k_x^2} \\ &= \sqrt{\left(\frac{\omega}{c}\right)^2 \varepsilon_i(\omega) - k_x^2} \end{aligned}$$



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Figure: 2DEG at a semiconductor heterojunction

Existence of Surface Waves

$$\varepsilon_1(\omega) \cdot \varepsilon_2(\omega) < 0$$

- Criterion met at terahertz frequency range
- Opposite signs of dielectric constant at Semiconductor interface
- GaAs/AlGaAs semiconductor heterostructures
- Strontium Titanate/Lanthanum Aluminate (STO/LAO) oxide interfaces

Spring 2017

Optical Nanoantennas

Introduction

 Near-field Scanning Electron Microscopy (NSOM)

Subwavelength confinement

- Directivity enhancement of Quantum emitters
- Surface waves

Surface Plasmon-Polaritons

Radiation Mechanism

Wavenumber Mismatch

 $E_c\,$ - Conduction band edge

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 E_f - Fermi level

Optical Nanoantennas

Dispersion Relation

Metal-dielectric Interface

$$egin{aligned} k_{sp} &= k_1 \sqrt{rac{arepsilon_1 arepsilon_2 (\omega)}{arepsilon_1 + arepsilon_2 (\omega)}} \ arepsilon_2 (\omega) &= arepsilon_\infty - rac{\omega_d^2}{\omega^2 + j \gamma \omega} + ext{C.P.terms} \end{aligned}$$

